

Description

The HPK616BA uses advanced trench technology to provide excellent R_{DS(ON)}, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

 $V_{DS} = 30V I_{D} = 70A$

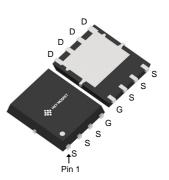
 $R_{DS(ON)} < 7 \text{ m}\Omega \text{ V}_{GS}=10\text{V}$

Application

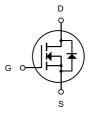
Battery protection

Load switch

Uninterruptible power supply



DFN5X6-8L (PDFN-8(5.8x4.9))



N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
HPK616BA	DFN5X6-8L(PDFN-8(5.8x4.9))	HXY MOSFET	5000

Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units		
Vos	Drain-Source Voltage	30	V		
Vgs	Gate-Source Voltage	Source Voltage ±20			
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ 10V ¹	rrent, V _{GS} @ 10V ¹ 70			
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ 10V ¹	is Drain Current, V _{GS} @ 10V ¹ 40			
Ірм	Pulsed Drain Current ² 140		А		
EAS	Single Pulse Avalanche Energy ³	115.2	mJ		
las	Avalanche Current	Avalanche Current 48			
P _D @T _C =25°C	Total Power Dissipation ⁴	ation ⁴ 59			
P _D @T _A =25°C	Total Power Dissipation ⁴	2	W		
Тѕтс	Storage Temperature Range	-55 to 150	°C		
TJ	Operating Junction Temperature Range	ure Range -55 to 150			
Reja	Thermal Resistance Junction-Ambient ¹	62	°C/W		
Rыс	Thermal Resistance Junction-Case ¹	I Resistance Junction-Case ¹ 2.1			



Electrical Characteristics (T_J=25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	30			V
∆BVpss/∆Tj	BVDSS Temperature Coefficient	Reference to 25°C , I _D =1mA		0.028		V/°C
RDS(ON)		V _{GS} =10V , I _D =30A		5.7	7	
	Static Drain-Source On-Resistance ²	V _{GS} =4.5V , I _D =15A		11	13	$m\Omega$
VGS(th)	Gate Threshold Voltage	\/oo=\/oo o =250uA	1.2		2.5	V
$\triangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	$V_{GS}=V_{DS}$, $I_D=250uA$		-6.16		mV/°0
loss	Drain-Source Leakage Current	V _{DS} =24V , V _{GS} =0V , T _J =25°C			1	
1000		V _{DS} =24V , V _{GS} =0V , T _J =55°C			5	uA
Igss	Gate-Source Leakage Current	V_{GS} = $\pm 20V$, V_{DS} = $0V$			±100	nA
gfs	Forward Transconductance	V _{DS} =5V , I _D =30A		43		S
R_g	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz		1.7		Ω
Qg	Total Gate Charge (4.5V)			20		
Qgs	Gate-Source Charge	V _{DS} =15V , V _{GS} =4.5V , I _D =15A		7.6		nC
Q _{gd}	Gate-Drain Charge			7.2		
Td(on)	Turn-On Delay Time			7.8		
Tr	Rise Time	V _{DD} =15V , V _{GS} =10V ,		15		ns
Td(off)	Turn-Off Delay Time	R _G =3.3		37.3		
Tf	Fall Time	_ I _D =15A		10.6		
Ciss	Input Capacitance			2295		
Coss	Output Capacitance	V _{DS} =15V , V _{GS} =0V , f=1MHz		267		рF
Crss	Reverse Transfer Capacitance			210		·
ls	Continuous Source Current ^{1,5}				81	Α
lsм	Pulsed Source Current ^{2,5}	V _G =V _D =0V , Force Current			160	Α
VsD	Diode Forward Voltage ²	V _{GS} =0V , I _S =1A , T _J =25°C			1	V
t _{rr}	Reverse Recovery Time			14		nS
	Reverse Recovery Charge	$_{\perp}$ IF=30A , dI/dt=100A/ μ s ,		5		nC

- 1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300 \text{us}$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is V_{DD} =25V, V_{GS} =10V,L=0.1mH, I_{AS} =48A 4.The power dissipation is limited by 150°C junction temperature
- 5. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.



Typical Characteristics

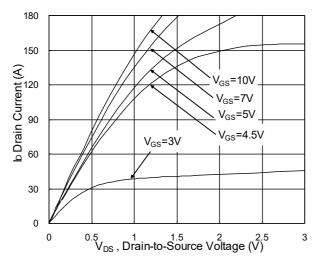


Fig.1 Typical Output Characteristics

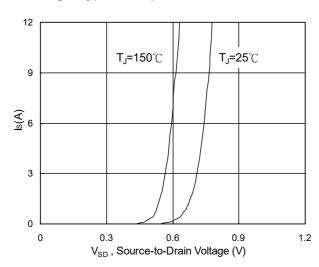


Fig.3 Forward Characteristics of Reverse

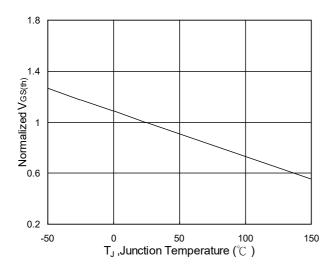


Fig.5 Normalized $V_{\text{GS(th)}}$ vs. T_{J}

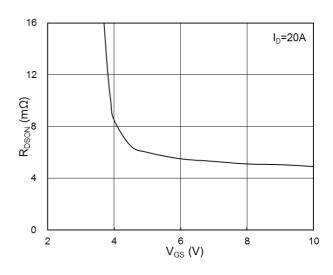


Fig.2 On-Resistance vs. G-S Voltage

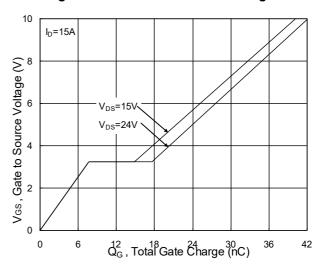


Fig.4 Gate-Charge Characteristics

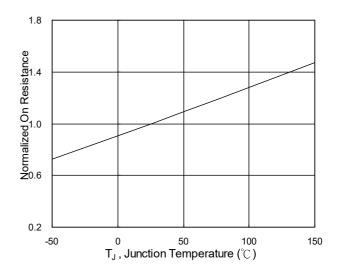
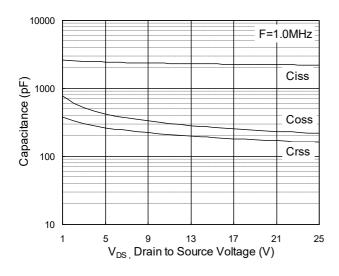


Fig.6 Normalized R_{DSON} vs. T_J



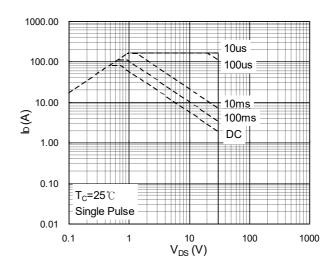


Fig.7 Capacitance

Fig.8 Safe Operating Area

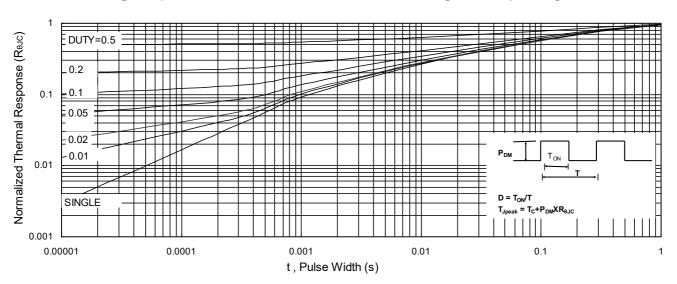


Fig.9 Normalized Maximum Transient Thermal Impedance

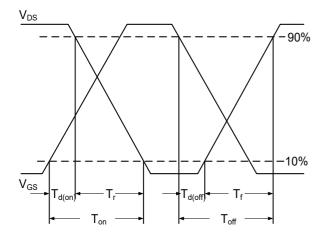


Fig.10 Switching Time Waveform

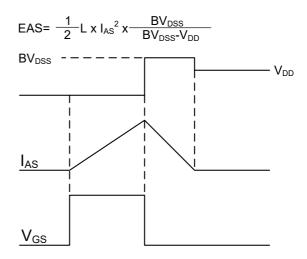
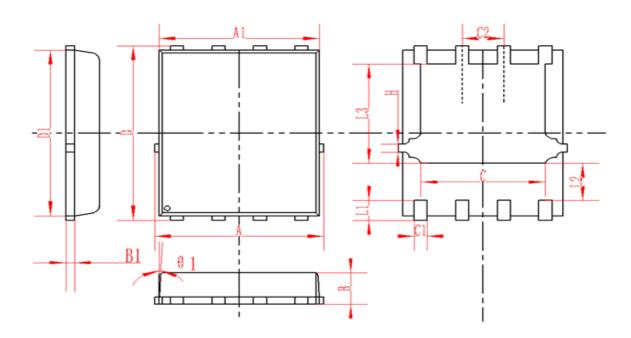


Fig.11 Unclamped Inductive Switching Waveform

DFN5X6-8L(PDFN-8(5.8x4.9)) Package Information



SYMBOL	MM		INCH			
	MIN	NOM	MAX	MIN	NOM	MAX
А	4.95	5	5.05	0.195	0.197	0.199
A1	4.82	4.9	4.98	0.190	0.193	0.196
D	5.98	6	6.02	0.235	0.236	0.237
D1	5.67	5.75	5.83	0.223	0.226	0.230
В	0.9	0.95	1	0.035	0.037	0.039
B1	0.254REF		0.010REF			
С	3.95	4	4.05	0.156	0.157	0.159
C1	0.35	0.4	0.45	0.014	0.016	0.018
C2	1.27TYP		0.5TYP			
θ1	8°	10°	12°	8°	10°	12°
L1	0.63	0.64	0.65	0.025	0.025	0.026
L2	1.2	1.3	1.4	0.047	0.051	0.055
L3	3.415	3.42	3.425	0.134	0.135	0.135
Н	0.24	0.25	0.26	0.009	0.010	0.010

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